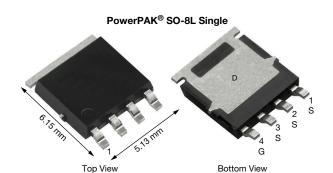


N-Channel 60 V (D-S) MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0045
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.0054
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 6 \text{ V}$	0.0078
Q _g typ. (nC)	15.5
I _D (A)	79.4
Configuration	Single

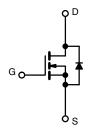
FEATURES

- TrenchFET® Gen IV power MOSFET
- Very low R_{DS} Q_g figure-of-merit (FOM)
- Tuned for the lowest R_{DS} Q_{oss} FOM
- 100 % R_a and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

COMPLIANT HALOGEN **FREE**

APPLICATIONS

- Synchronous rectification
- · Primary side switch
- DC/DC converter
- · Motor drive switch



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SiJ186DP-T1-GE3

ABSOLUTE MAXIMUM RATING	S (T _A = 25 °C, u	ınless otherw	vise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	60	M	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		79.4		
	T _C = 70 °C	1 . [63.5		
	T _A = 25 °C	I _D	23 ^{b, c}		
	T _A = 70 °C	1 [18.4 ^{b, c}	•	
Pulsed drain current (t = 100 μs)		I _{DM}	150	A	
Carting and a supply of the state of the sta	T _C = 25 °C		51.8		
Continuous source-drain diode current	T _A = 25 °C	l _s	4.5 b, c		
Single pulse avalanche current L = 0.1 mH		I _{AS}	25		
Single pulse avalanche energy		E _{AS}	31.25	mJ	
	T _C = 25 °C		57		
Mandan and a sure discipation	T _C = 70 °C	1 , [36	W	
Maximum power dissipation	T _A = 25 °C	P _D	5 b, c	VV	
	T _A = 70 °C	İ	3.2 b, c		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) c			260		

THERMAL RESISTANCE RAT	INGS				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	t ≤ 10 s	R_{thJA}	20	25	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.7	2.2	C/VV

Notes

- Package limited
 Surface mounted on 1" x 1" FR4 board

S18-0824-Rev. A, 13-Aug-2018

- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 70 °C/W $T_C = 25$ °C



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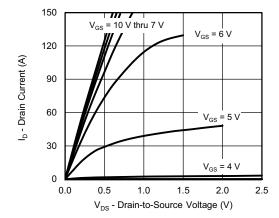
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	32	-	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-6.7	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	3.6	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	-	-	15	μA
On-state drain current a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	Α
		$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	-	0.0037	0.0045	
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 10 \text{ A}$	-	0.0043	0.0054	Ω
		$V_{GS} = 6 \text{ V}, I_D = 10 \text{ A}$	-	0.0060	0.0078	
Forward transconductance ^a	9fs	V _{DS} = 15 V, I _D = 15 A	-	54	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	1710		
Output capacitance	C _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	445	-	рF
Reverse transfer capacitance	C _{rss}		-	29	-	
<u> </u>		$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$	-	24.5	37	
Total gate charge	Q _g		-	15.5	24	_
Gate-source charge	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 6 \text{ V}, I_D = 10 \text{ A}$	-	6.5	-	nC
Gate-drain charge	Q _{gd}	20 1 00 1 2	-	4.5	-	_
Output charge	Q _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	27.5	-	_
Gate resistance	R _q	f = 1 MHz	0.3	0.85	1.5	Ω
Turn-on delay time	t _{d(on)}		-	10	20	
Rise time	t _r	$V_{DD} = 30 \text{ V}, R_L = 3 \Omega, I_D \cong 10 \text{ A},$	_	22	44	
Turn-off delay time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_q = 1 \Omega$	-	14	28	
Fall time	t _f	Ü	-	9	18	
Turn-on delay time	t _{d(on)}		-	11	22	ns
Rise time	t _r	$V_{DD} = 30 \text{ V}, R_1 = 3 \Omega, I_D \cong 10 \text{ A},$	-	23	46	_
Turn-off delay time	t _{d(off)}	$V_{GEN} = 7.5 \text{ V}, R_q = 1 \Omega$	_	13	26	
Fall time	t _f	Ü	_	9	18	
Drain-Source Body Diode Characteristi	· · · · · · · · · · · · · · · · · · ·			ļ		ļ
Continuous source-drain diode current	I _S	T _C = 25 °C	_	_	51.8	
Pulse diode forward current	I _{SM}	<u> </u>	_	_	150	Α
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	_	0.77	1.1	V
Body diode reverse recovery time	t _{rr}	15 - 5 / 1, vG5 - 0 v	-	44	88	ns
Body diode reverse recovery time	Q _{rr}	L = 10 A di/dt = 100 A/vo	-	42	84	nC
Reverse recovery fall time	t _a	$I_F = 10 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s,}$ $T_{.1} = 25 ^{\circ}\text{C}$	_	20	04	110
						1

Notes

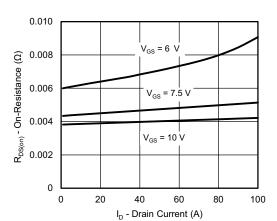
- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

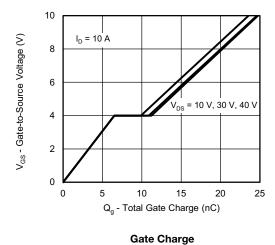




Output Characteristics

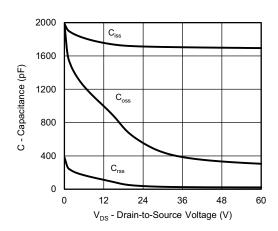


On-Resistance vs. Drain Current and Gate Voltage

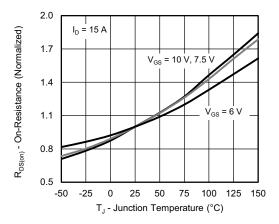


120
96
(Y) the true of the tru

Transfer Characteristics

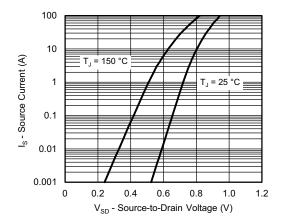


Capacitance

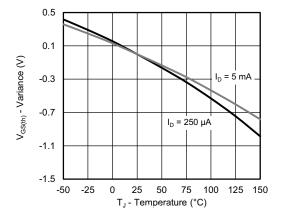


On-Resistance vs. Junction Temperature

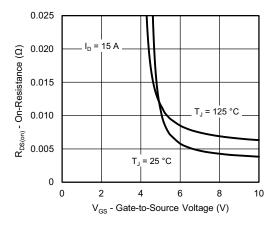




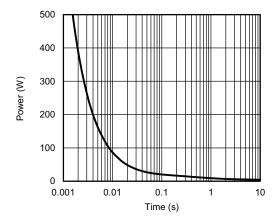
Source-Drain Diode Forward Voltage



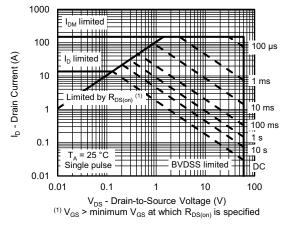
Threshold Voltage



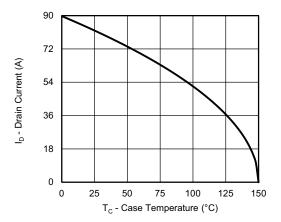
On-Resistance vs. Gate-to-Source Voltage



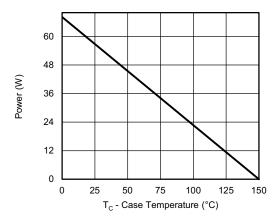
Single Pulse Power, Junction-to-Ambient



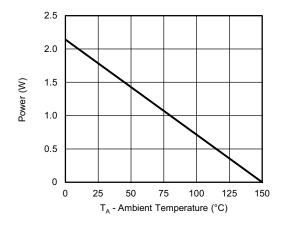
Safe Operating Area, Junction-to-Ambient



Current Derating a





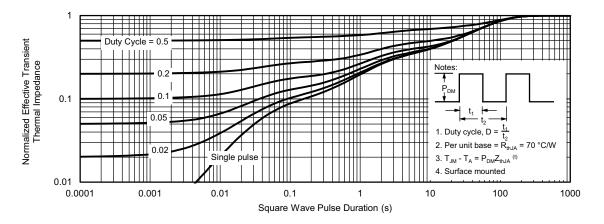


Power, Junction-to-Ambient

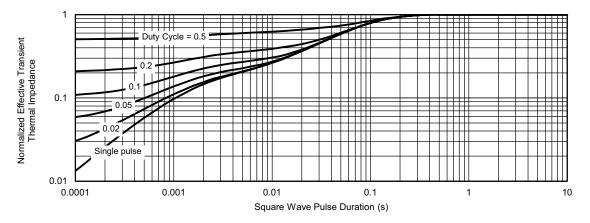
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient

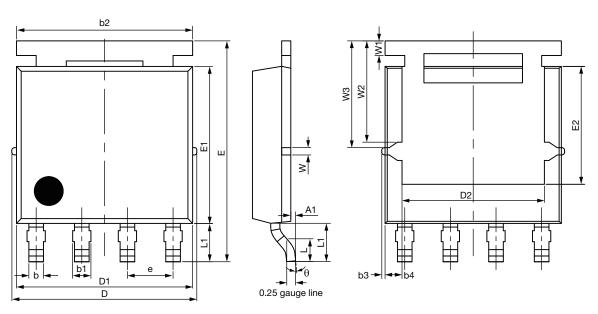


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76825.

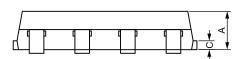


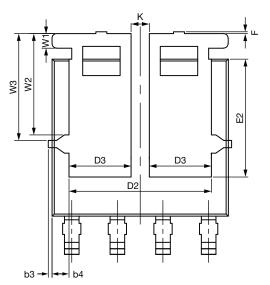
PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23		0.009				
W1	0.41		0.016				
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. E, 05-Aug-2019

DWG: 5976

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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